

Switching diode

DAN217U / BAV99U *1 / DAN217

*1 BAV99U is only sold in countries other than Japan.

●Application

Ultra high speed switching

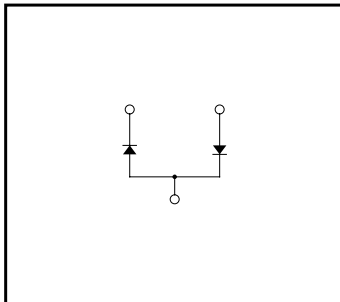
●Features

- 1) Small surface mounting type. (UMD3,SMD3)
- 2) Two diode elements are connected in series
($V_F \times 2$) per circuit.

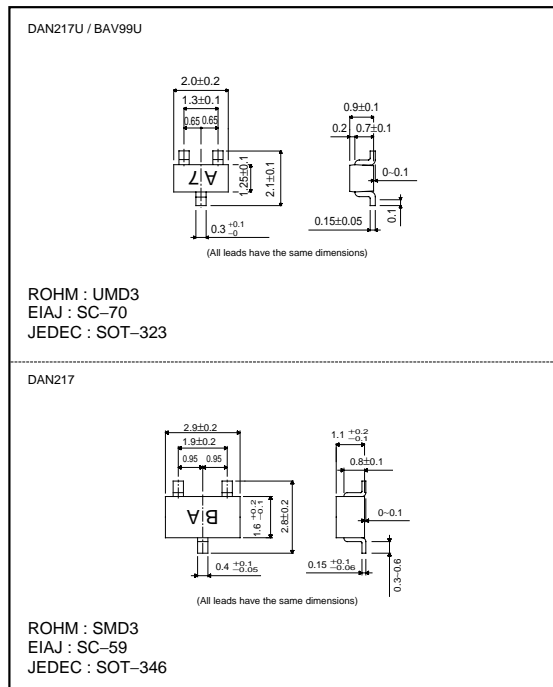
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Type	Peak reverse voltage $V_{RM}(V)$	DC reverse voltage $V_R(V)$	Peak forward current $I_{FM}(mA)$	Mean rectifying current $I_o(mA)$	Surge current (1 μ s) $I_{surge}(mA)$	Power dissipation (TOTAL) $P_d(mW)$	Junction temperature $T_j(^{\circ}C)$	Storage temperature $T_{stg}(^{\circ}C)$
DAN217U	80	80	300	100	4000	200	150	-55 ~ +150
BAV99U	80	80	300	100	4000	200	150	-55 ~ +150
DAN217	80	80	300	100	4000	200	150	-55 ~ +150

Diodes

●Electrical characteristics (Ta=25°C)

Type	Forward voltage		Reverse current		Fig
	V _F (V) Max.	Cond. I _F (mA)	I _R (μA) Max.	Cond. V _R (V)	
DAN217U	1.2	100	0.2	70	1 ~ 3
BAV99U	1.2	100	0.2	70	1 ~ 3
DAN217	1.2	100	0.1	70	4 ~ 6

●Electrical characteristic curves (Ta=25°C)

(DAN217U,BAV99U)---Fig.1~3

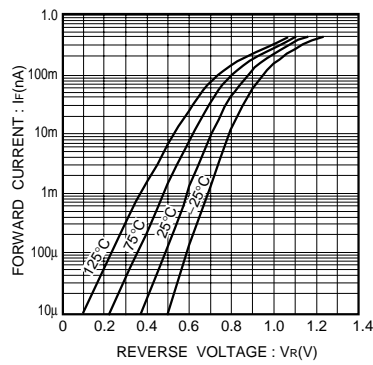


Fig.1 Forward characteristics

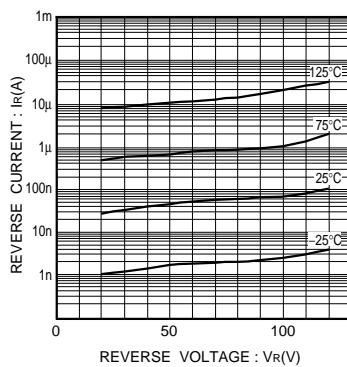


Fig.2 Reverse characteristics

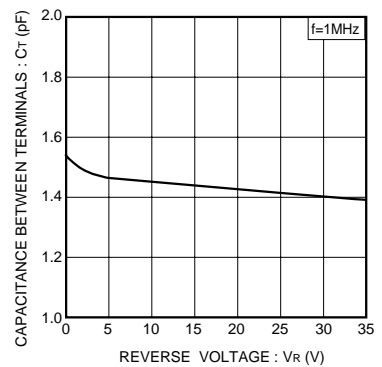


Fig.3 Capacitance between terminals characteristics

(DAN217) ---Fig.4~6

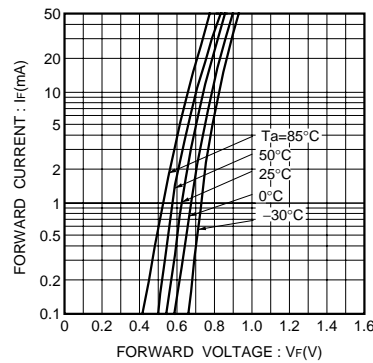


Fig.4 Forward characteristics

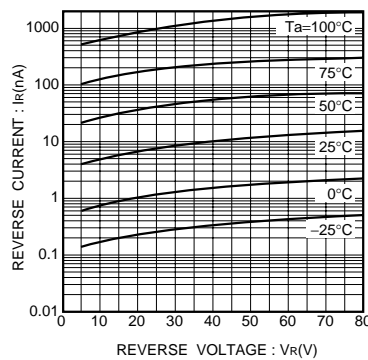


Fig.5 Reverse characteristics

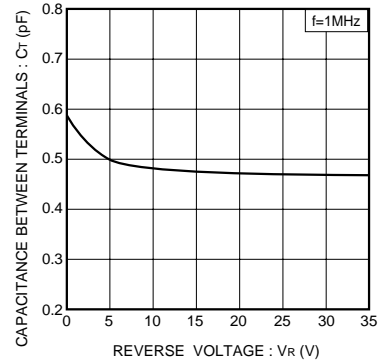


Fig.6 Capacitance between terminals characteristics